

# BAS40HP-HAF

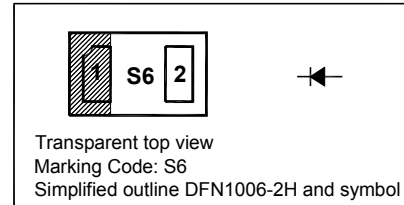
## Silicon Epitaxial Planar Schottky Barrier Diode

### Features

- Low forward voltage
- Fast switching
- Halogen and Antimony Free(HAF), RoHS compliant

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	40	V
DC Blocking Voltage	$V_R$	40	V
Forward Continuous Current	$I_F$	200	mA
Peak Forward Surge Current (at $t_p = 8.3$ ms)	$I_{FSM}$	600	mA
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{Stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25^\circ\text{C}$

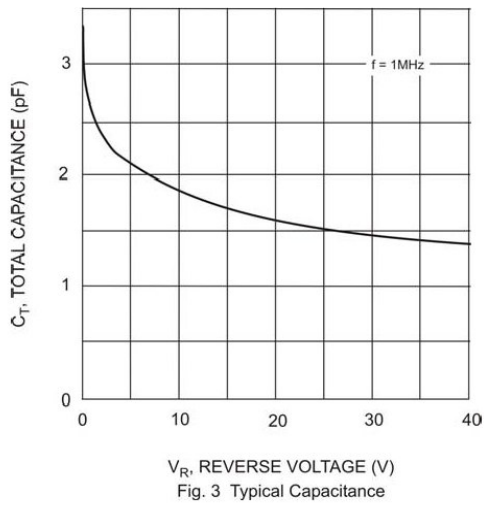
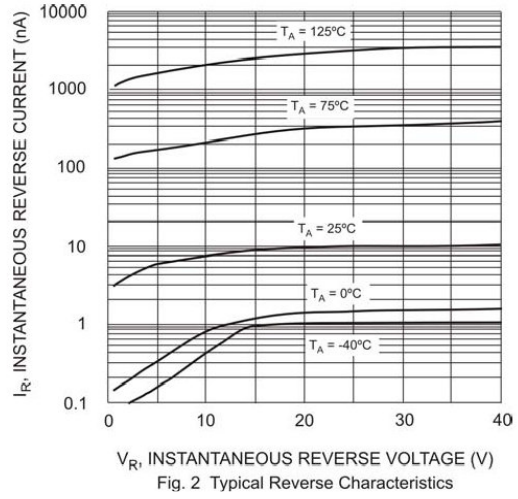
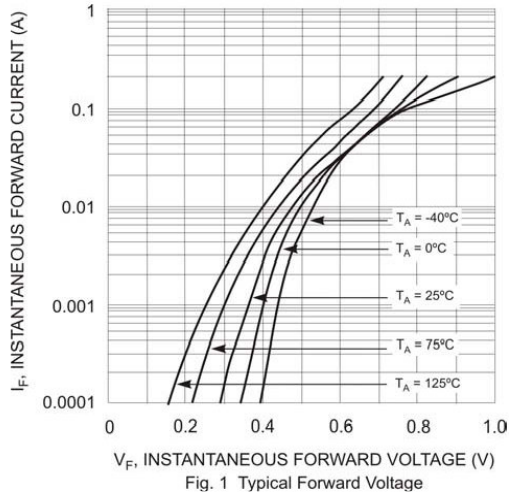
Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 10 \mu\text{A}$	$V_{(BR)R}$	40	-	V
Forward Voltage at $I_F = 1$ mA at $I_F = 40$ mA	$V_F$ $V_F$	- -	0.38 1	V V
Reverse Current at $V_R = 30$ V	$I_R$	-	200	nA
Reverse Recovery Time at $I_F = I_R = 10$ mA to $I_R = 1$ mA, $R_L = 100 \Omega$	$t_{rr}$	-	5	ns
Capacitance at $V_R = 0$ V, $f = 1$ MHz	$C_j$	-	5	pF

**TOP DYNAMIC**



Dated: 18/05/2015 Rev: 04

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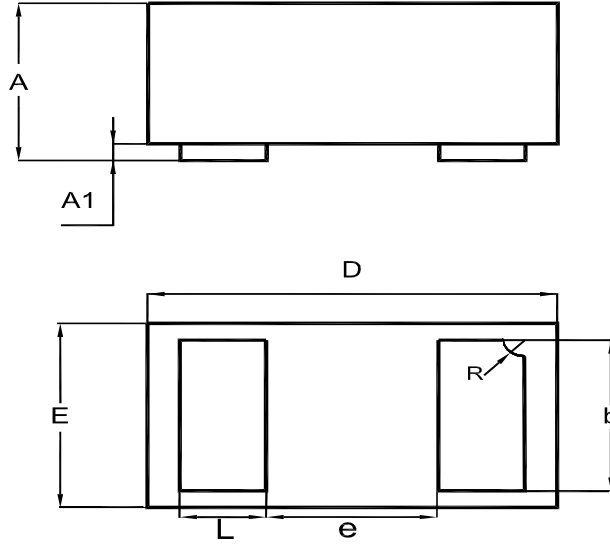
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## PACKAGE OUTLINE

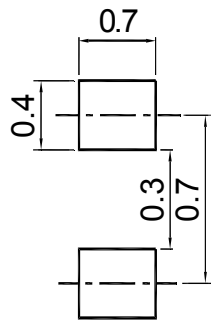
Plastic surface mounted package

DFN1006-2H



UNIT	A	A1	b	D	E	e	L	R
mm	0.51	0.05	0.55	1.05	0.65	0.4	0.3	0.15
	0.46	0	0.45	0.95	0.55		0.2	0.05

## Recommended Soldering Footprint



## Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
DFN1006-2H	8	4 ± 0.1	0.157 ± 0.004	178	7	5,000

**TOP DYNAMIC**



ISO14001 : 2004 Certificate No. 121505007  
ISO 9001 : 2008 Certificate No. 01141012  
OHSAS 18001 : 2007 Certificate No. 05191506008  
IECQ QC 080000 Certificate No. E241800074482

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